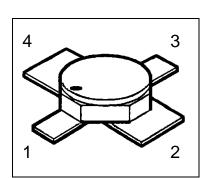


### **BFY405(ES)**

#### **Features**

- For Low Current Applications
- For Oscillators up to 12 GHz
- Noise Figure F = 1.15 dB at 1.8 GHz
   Outstanding G<sub>ms</sub> = 23dB at 1.8 GHz
- Hermetically sealed microwave package
- Transition Frequency  $f_T = 20 \text{ GHz}$
- SIEGET<sup>®</sup>25-Line
   Infineon Technologies Grounded Emitter Transistor-25 GHz f<sub>T</sub>-Line



#### **Product validation**

• **@esa** Space Qualified

ESCC Detail Spec. No.: 5611/008 Type Variant No. 01

# **Description**

**ESD**: Electrostatic discharge sensitive device, observe handling precautions!

Table 1 Product information

Туре	Comment	Pin Config	Package			
		1	2	3	4	
BFY405(ES)	For flight use		_	Б	_	Minus V
BFY405(P) <sup>1</sup>	Not for flight use <sup>1</sup>		E	В	E	Micro-X

<sup>&</sup>lt;sup>1</sup> (P) parts have the same fit, form and function as (ES) parts, no screening acc. to Chart F3 in ESCC Generic Specification No. 5010

## **BFY405(ES)**

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## **Table of contents**

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## **BFY405(ES)**

**Maximum ratings** 



#### **Maximum ratings** 1

Table 2 **Maximum ratings** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Тур.	Мах.		
Collector-emitter voltage	$V_{\sf CEO}$	-	-	4.5	V	
Collector-base voltage	$V_{CBO}$	-	-	15	V	
Emitter-base voltage	$V_{EBO}$	-	-	1.5	V	
Collector current	I <sub>C</sub>	-	-	12	mA	
Base current	I <sub>B</sub>	-	-	1	mA	
Total power dissipation <sup>1</sup>	P <sub>tot</sub>	-	-	55	mW	<i>T</i> <sub>S</sub> ≤ 145 °C
Junction temperature	T <sub>j</sub>	-	-	175	°C	
Operating temperature	Top	-65	-	175	°C	
Storage temperature	$T_{ m stg}$	-65	-	175	°C	

 $<sup>^{1}</sup>$  For  $T_{S} > 145$  °C derating is required.  $T_{S}$  is measured on the collector lead at the soldering point to the PCB

## BFY405(ES)

Thermal characteristics



# 2 Thermal characteristics

### Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition	
		Min.	Тур.	Max.			
Thermal resistance, junction –soldering point	$R_{th,JS}$	-	-	545	K/W	T <sub>S</sub> is measured on the collector lead at the soldering point to the PCB	
Soldering Temperature	$T_{ m sol}$	-	-	250	°C	Duration 5 seconds maximum at a distance of not less than 0.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.	

### **BFY405(ES)**

#### **Electrical characteristics**



Issue 5, January 2022

## **3** Electrical characteristics

at  $T_A$ =25°C, unless otherwise specified

**Table 4** Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition	
		Min.	Тур. Мах.				
Collector-base cutoff current	I <sub>CBO</sub>	-	-	10	nA	$V_{\rm CB} = 5V, I_{\rm E} = 0A$	
Collector-emitter cutoff current <sup>1</sup>	I <sub>CEX</sub>	-	-	20	μΑ	$V_{CE} = 4.5V, I_B = 0.1 \mu A$	
Emitter base cuttoff current	I <sub>EBO</sub>	-	-	5	μΑ	$V_{\rm EB} = 1.5 \text{V}, I_{\rm C} = 0 \text{A}$	
DC current gain	h <sub>FE</sub>	50	90	150	-	$I_{\rm C} = 5 {\rm mA},  V_{\rm CE} = 1 {\rm V}$	

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition	
		Min.	Тур.	Max.			
Transition frequency	$f_{T}$	20	22	-	GHz	$I_{C}$ = 10mA, $V_{CE}$ = 3V, $f$ = 2GHz	
Collector-base capacitance	Ссв	-	0.05	0.9	pF	$V_{CB}$ = 2V, $V_{BE}$ = vbe= 0, f= 1MHz	
Collector-emitter capacitance	C <sub>CE</sub>	-	0.32	0.48	pF	V <sub>CE</sub> = 2V, V <sub>BE</sub> = vbe= 0, f= 1MHz	
Emitter-base capacitance	C <sub>EB</sub>	-	0.36	3	pF	V <sub>EB</sub> =0.5V, V <sub>CB</sub> = vcb= 0, f= 1MHz	
Noise Figure	F	-	1.15	1.8	dB	$I_{C}$ = 2mA, $V_{CE}$ = 2V, $f$ = 1.8GHz, $Z_{S}$ = $Z_{Sopt}$	
Insertion power gain	$ S_{21e} ^2$	14	18	-	dB	$I_{C} = 5 \text{mA}, V_{CE} = 2 \text{V}, f = 1.8 \text{GHz},$ $Z_{S} = Z_{L} = 50 \Omega$	
Power Gain <sup>2</sup>	$G_{ms}$	-	23	-	dB	$I_{C}$ = 5mA, $V_{CE}$ = 2V, $f$ = 1.8GHz, $Z_{S}$ = $Z_{Sopt}$ , $Z_{L}$ = $Z_{Lopt}$	
1dB Compression point	P <sub>-1dB</sub>	-	5	-	dBm	$I_{C}$ = 5mA, $V_{CE}$ = 2V, $f$ = 1.8GHz, $Z_{S}$ = $Z_{Sopt}$ , $Z_{L}$ = $Z_{Lopt}$	

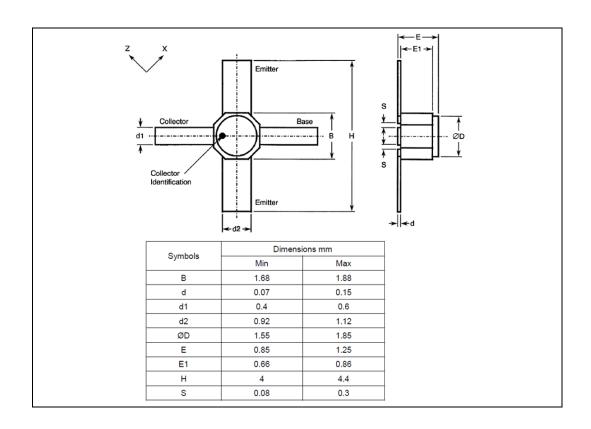
$$G_{ms} = \left| \frac{S21}{S12} \right|$$

 $<sup>^{1}</sup>$  This test assures  $V_{(BR)CE0} > 4.5V$ 

#### **Package outlines**



## 4 Package outlines



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